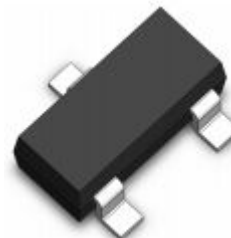


Description

The Si2323CDS uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

Dimensions SOT-23



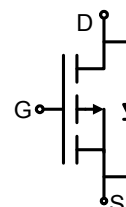
General Features

$V_{DS} = -20V$ $I_D = -4.9A$
 $R_{DS(ON)} < 38m\Omega$ @ $V_{GS} = -4.5V$

Application

- Battery protection
- Load switch
- Uninterruptible power supply

Pin Configuration



Package Marking and Ordering Information

Device	Device Marking	Device Package	Reel Size	Tape width	Quantity
Si2323CDS	A5SHB	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (TC=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-4.9	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-3.9	A
I_{DM}	Pulsed Drain Current ²	-14	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation ³	1.31	W
$P_D @ T_A = 70^\circ C$	Total Power Dissipation ³	0.84	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	120	°C/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹ (t ≤ 10s)	95	°C/W

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-20	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.014	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-4.5V, I _D =-4.9A	---	32	38	mΩ
		V _{GS} =-2.5V, I _D =-3.4A	---	45	55	
		V _{GS} =-1.8V, I _D =-2A	---	65	85	
V _{GS(th)}	Gate Threshold Voltage		-0.4	---	-1.0	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient	V _{GS} =V _{DS} , I _D =-250uA	---	3.95	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-16V, V _{GS} =0V, T _J =25°C	---	---	-1	uA
		V _{DS} =-16V, V _{GS} =0V, T _J =55°C	---	---	-5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±12V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-3A	---	12.8	---	S
Q _g	Total Gate Charge (-4.5V)		---	10.2	14.3	nC
Q _{gs}	Gate-Source Charge	V _{DS} =-15V, V _{GS} =-4.5V, I _D =-3A	---	1.89	2.6	
Q _{gd}	Gate-Drain Charge		---	3.1	4.3	
T _{d(on)}	Turn-On Delay Time		---	5.6	11.2	ns
T _r	Rise Time	V _{DD} =-10V, V _{GS} =-4.5V,	---	40.8	73	
T _{d(off)}	Turn-Off Delay Time	R _G =3.3, I _D =-3A	---	33.6	67	
T _f	Fall Time		---	18	36	
C _{iss}	Input Capacitance		---	857	1200	pF
C _{oss}	Output Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	---	114	160	
C _{rss}	Reverse Transfer Capacitance		---	108	151	
I _S	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	-4.9	A
I _{SM}	Pulsed Source Current ^{2,4}		---	---	-14	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1	V
t _{rr}	Reverse Recovery Time	I _F =-3A, di/dt=100A/μs,	---	21.8	---	nS
Q _{rr}	Reverse Recovery Charge	T _J =25°C	---	6.9	---	nC

Note :

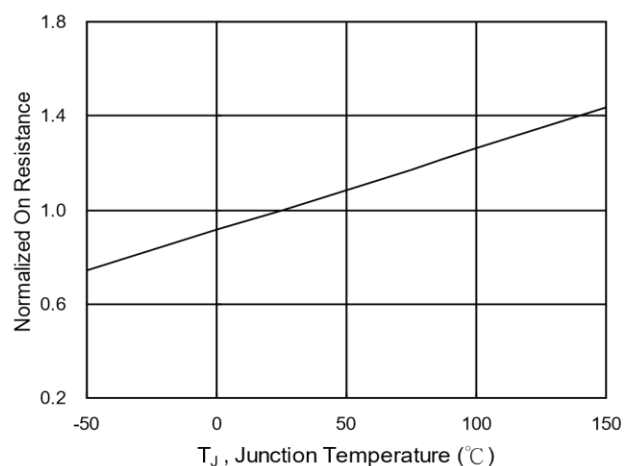
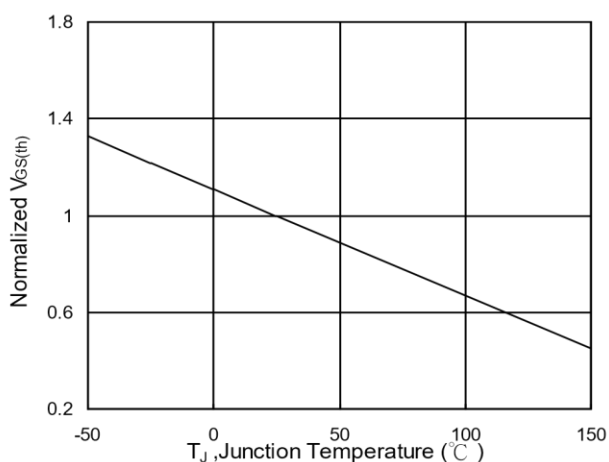
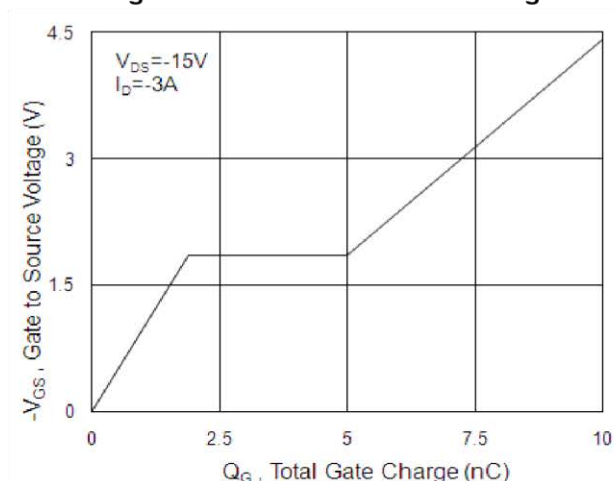
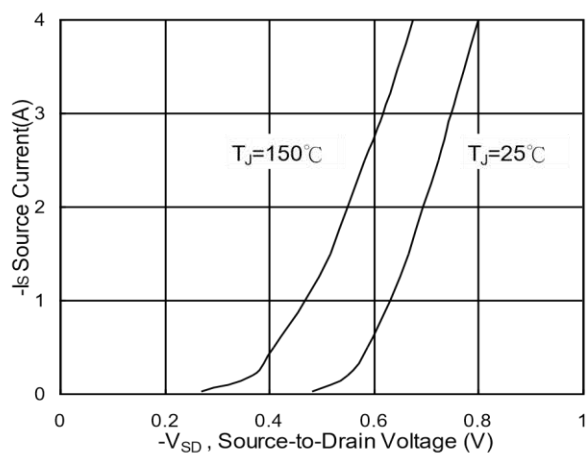
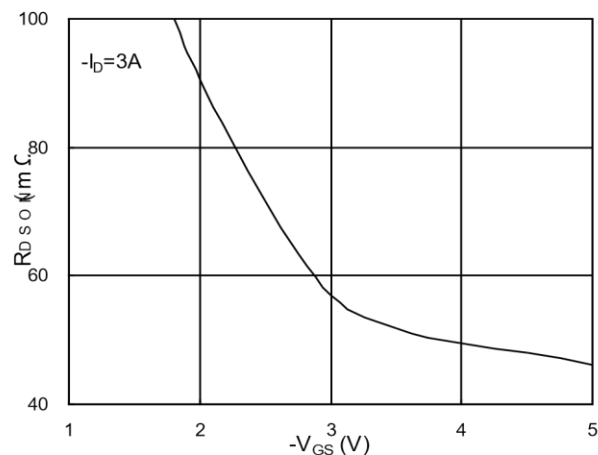
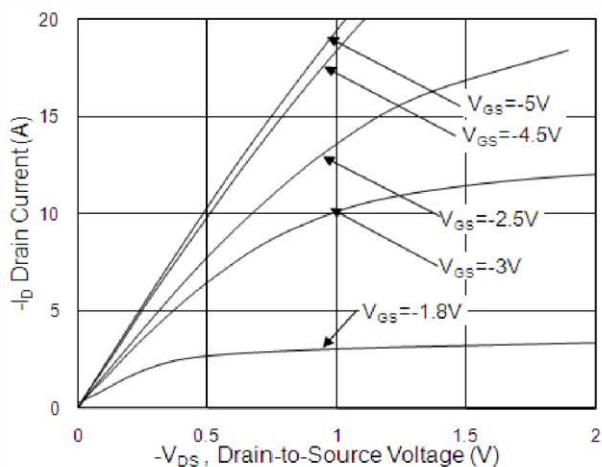
1 .The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width Δ 300us , duty cycle Δ 2%

3.The power dissipation is limited by 150°C junction temperature

4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics



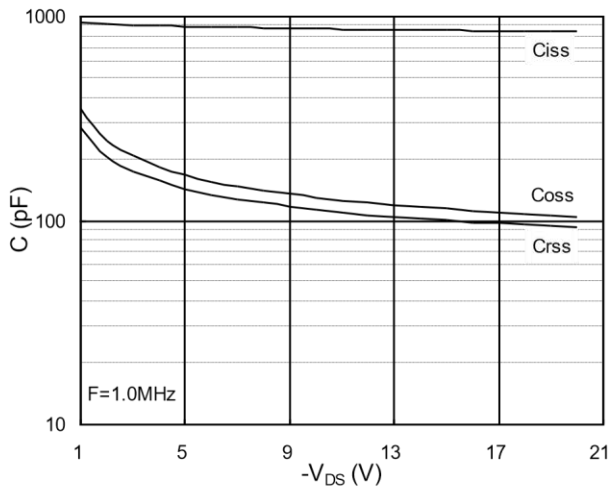


Fig.7 Capacitance

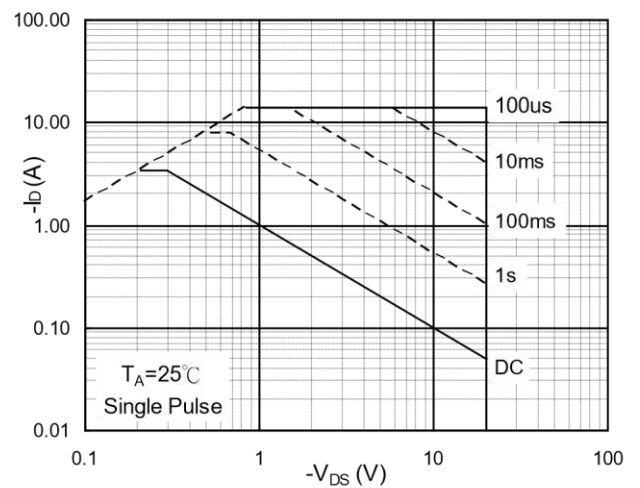


Fig.8 Safe Operating Area

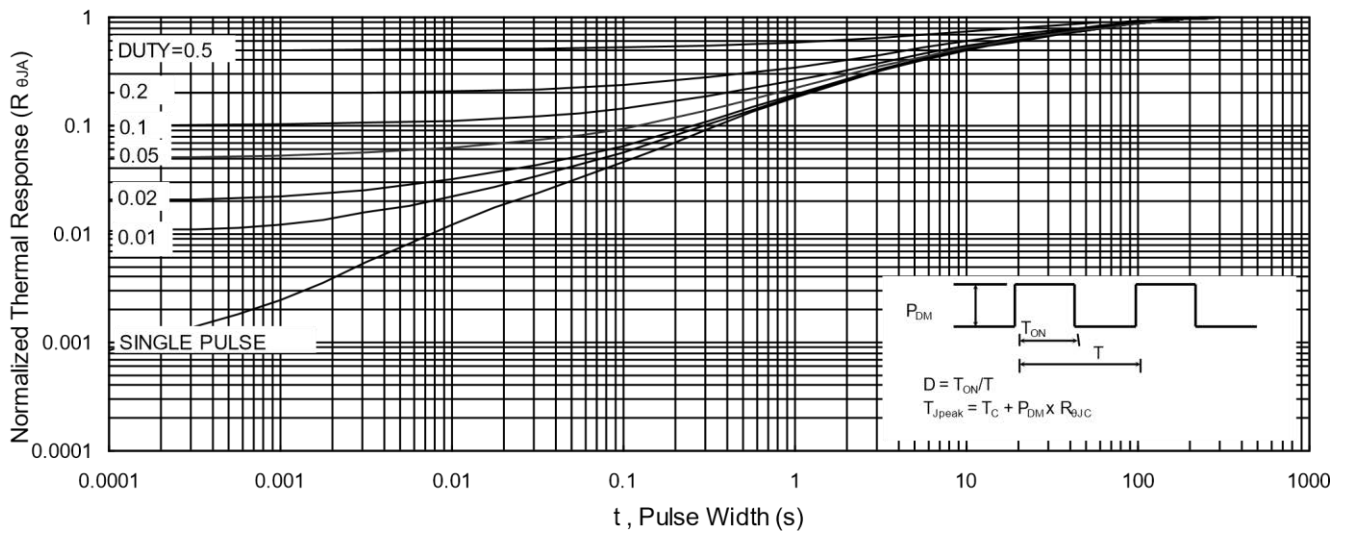


Fig.9 Normalized Maximum Transient Thermal Impedance

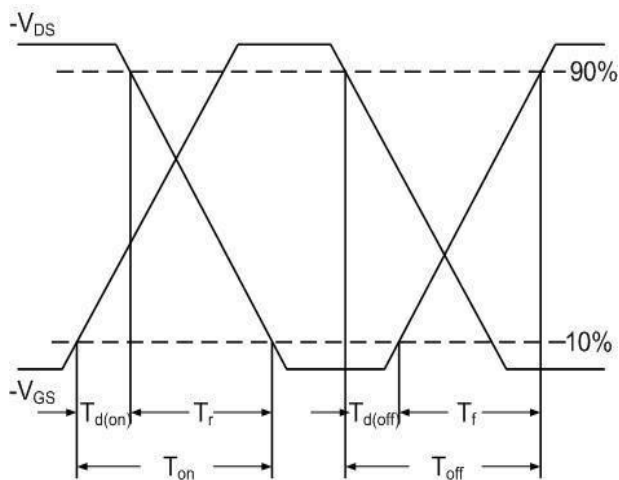


Fig.10 Switching Time Waveform

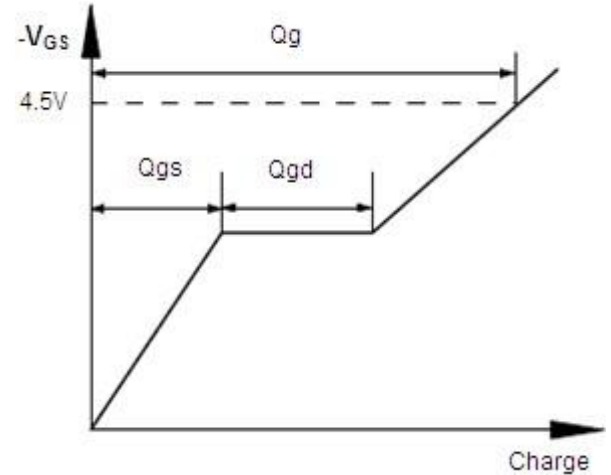
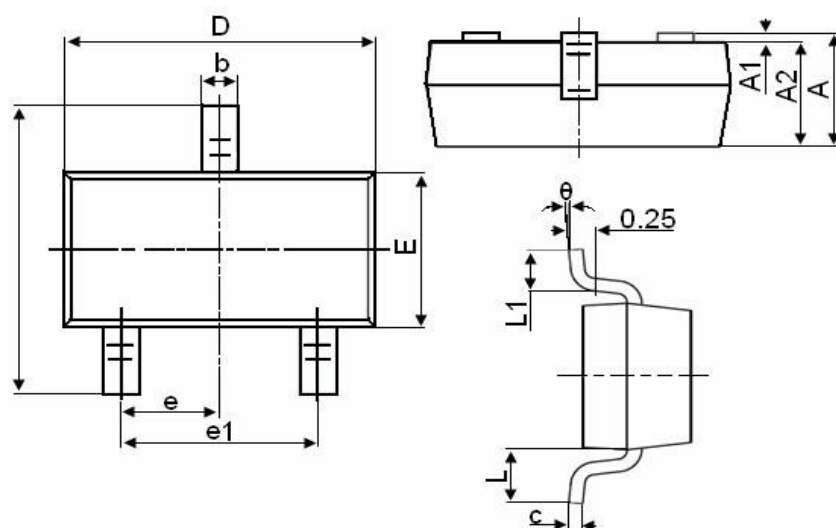


Fig.11 Gate Charge Waveform

Package Mechanical Data-SOT-23



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°